

# PROCESS CP188

## Small Signal Transistor

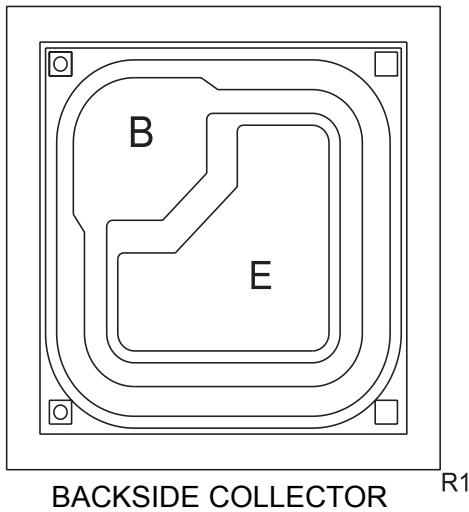
[查询"NPN 188"供应商](#) NPN Low Noise Amplifier Transistor Chip

**Central**<sup>TM</sup>  
Semiconductor Corp.

### PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	15 x 15 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	4.0 x 4.0 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

### GEOMETRY



### GROSS DIE PER 4 INCH WAFER

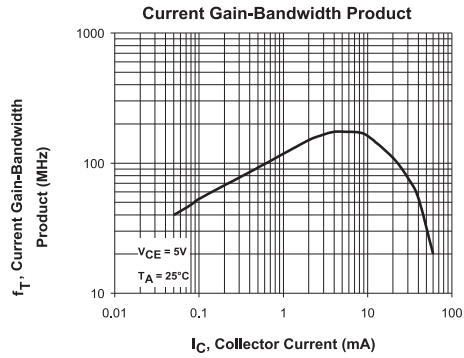
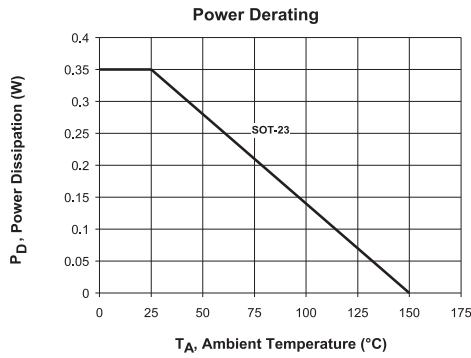
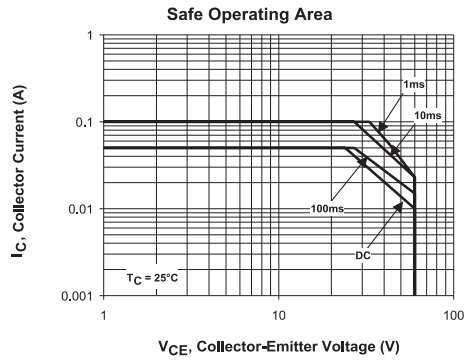
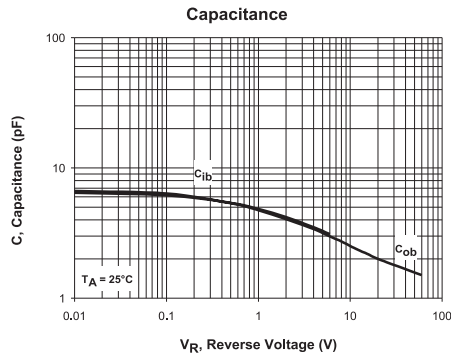
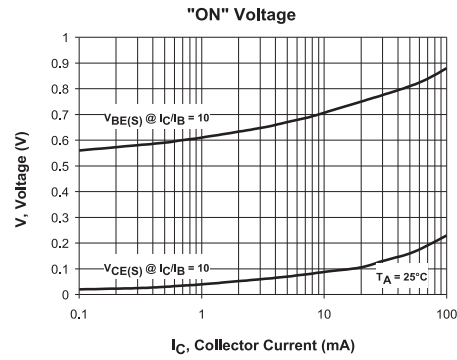
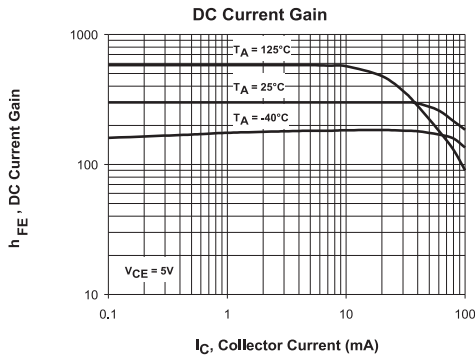
53,730

### PRINCIPAL DEVICE TYPES

CMPT2484  
CMPT5088  
CMPT5089  
CMPT6428  
CMPT6429  
2N2484

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centrasemi.com](http://www.centrasemi.com)

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